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(54) **INTEGRATED ASSEMBLIES AND METHODS OF FORMING INTEGRATED ASSEMBLIES**

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(57) **ABSTRACT**

Some embodiments include an integrated assembly having a first bottom electrode adjacent to a second bottom electrode. An intervening region is directly between the first and second bottom electrodes. Capacitor-insulative-material is adjacent to the first and second bottom electrodes. The capacitor-insulative-material is substantially not within the intervening region. Top-electrode-material is adjacent to the capacitor-insulative-material. Some embodiments include methods of forming integrated assemblies.